

Type	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition
76 BRS	1175	(silicon adj nitride) and (conduct\$4 near2 band)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/16 09:32		
77 BRS	37	(silicon adj nitride) near20 (conduct\$4 near2 band)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/16 09:50		
78 BRS	35	(silicon adj carbide) near20 (valence near2 band)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/16 20:00		
79 BRS	6	4980736.URPN.	USPAT	2004/03/16 10:14		
80 BRS	6	("4887134" "4931661" "4933731" "4980736" "4982255" "5101255").PN.	USPAT	2004/03/16 10:38		
81 BRS	2	6064091.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/16 20:34		
82 BRS	1	1999-371433.NRAN.	DERWENT	2004/03/16 20:05		
83 BRS	1243	(polycrystalline near2 (silicon or si)) and (250/\$ or 348/\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/16 20:38		
84 BRS	3	(polycrystalline near2 (silicon or si)) and (250/\$ or 348/\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/16 20:35		
85 BRS	288	(polycrystalline near2 (silicon or si) near10 substrate) and (250/\$ or 348/\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/16 20:36		
86 BRS	26	(polycrystalline near2 (silicon or si) adj substrate) and (250/\$ or 348/\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/16 20:41		
87 BRS	684	(polycrystalline adj (silicon or si) adj substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/16 21:20		
88 BRS	2	4496981.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/16 20:51		

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89	BRS	4	(microcrystalline adj (silicon or si) adj substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/16 22:00		
90	BRS	10	(microcrystalline near4 (silicon or si) adj substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/16 21:29		
91	BRS	348	(microcrystalline near10 (silicon or si) near10 substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/16 21:24		
92	BRS	15	((microcrystal\$6 micro-crystal\$6 (micro adj crystal\$6)) near4 (silicon or si) adj substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/16 21:33		
93	BRS	3429	((microcrystal\$6 micro-crystal\$6 (micro adj crystal\$6)) near4 (silicon or si))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/16 21:34		
94	BRS	122	((microcrystal\$6 micro-crystal\$6 (micro adj crystal\$6)) near4 (silicon or si)) and (348/\$ or 250/\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/16 21:35		
95	BRS	59	microcrystalline near10 polycrystalline near10 monocrystalline	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/16 22:07		
96	BRS	2	6077752.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/16 22:38		
97	BRS	2	6157072.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/16 22:46		
98	BRS	2	5635327.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/16 22:54		
99	BRS	2	4980736.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/16 22:57		
100	BRS	2	6,157,072.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/16 22:57		

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63	BRS	2	5122431.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 20:14		
64	BRS	129	canon and (electric\$4 near2 field near2 (relax\$4 or reduc\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 21:18		
65	BRS	2	"09102627"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/16 07:11		
66	BRS	0	9102627.URPN.	USPAT	2004/03/15 21:18		
67	BRS	0	9102627.URPN.	USPAT	2004/03/15 21:18		
68	BRS	1	1997-278784.NRAN.	DERWENT	2004/03/15 21:18		
69	BRS	2	4980736.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/16 07:30		
70	BRS	21599	(348/\$.ccls.) and (equal or "same" near5 (conduct\$4 adj band))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/16 07:33		
71	BRS	301	((348/\$.ccls.) and (equal or "same" near5 (conduct\$4 adj band))) and (amorphous)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/16 07:32		
72	BRS	23	((348/\$.ccls.) and (equal or "same" near5 (conduct\$4 adj band))) and (amorphous)) and (sic or (si-c) or (silicon adj carbide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/16 07:32		
73	BRS	1	(348/\$.ccls.) and ((equal or "same") near5 (conduct\$4 adj band))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/16 07:34		
74	BRS	2926	((equal or "same" or level\$4) near5 (conduct\$4 adj band))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/16 07:35		
75	BRS	566	((equal or "same") near5 (conduct\$4 adj band))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/16 09:31		

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52 BRS	218	si-c and si-n	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 15:50		
53 BRS	87	(si-c and si-n) and amorphous	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 16:05		
54 BRS	10548	(c/si or (carbon near5 silicon) or (c near4 si)) near20 (ratio or fraction or percent\$4 or proportion\$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 19:31		
55 BRS	5545	(c/si or (carbon near2 silicon) or (c near2 si)) near10 (ratio or fraction or percent\$4 or proportion\$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 16:07		
56 BRS	4372	(c/si or (carbon near2 silicon) or (c near2 si)) near5 (ratio or fraction or percent\$4 or proportion\$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 16:07		
57 BRS	3270	(c/si or (carbon near2 silicon) or (c near2 si)) near2 (ratio or fraction or percent\$4 or proportion\$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 16:07		
58 BRS	376	(c/si or si/c) near5 (ratio or fraction or percent\$4 or proportion\$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 16:08		
59 BRS	45	((c/si or si/c) near5 (ratio or fraction or percent\$4 or proportion\$6)) and (348/\$ or 257/\$ or 250/\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 16:16		
60 BRS	58	canon and (generat\$9 near2 multiplic\$8)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 17:15		
61 BRS	2	6064091.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 17:15		
62 BRS	2	6,157,072.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 20:04		